

a MOS capacitor comprising first and second terminals, wherein said first terminal is connected to a power source wire;

a ground potential wire connected between said ground terminal and said second terminal of said MOS capacitor, wherein said ground potential wire further comprises a connection point disposed between said ground terminal and said second terminal of said MOS capacitor such that the wire resistance between said ground terminal and said connection point is greater than the wire resistance between said second terminal and said connection point; and

an electrostatic protection element connected between said power source wire and said connection point so that said electrostatic protection element is in parallel with said MOS capacitor.

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22. (New) The semiconductor integrated circuit device according to claim 21, wherein no other diffusion layer except said electrostatic protection element is connected on said ground potential wire between said ground terminal and said connection point on said ground potential wire.

23. (New) The semiconductor integrated circuit device according to claim 21, wherein said power source wire is connected to a power source terminal to which a predetermined power source voltage is supplied.

24. (New) The semiconductor integrated circuit device according to claim 21, wherein said power source wire is connected to a power source terminal and a first power source voltage is supplied through a power source conversion circuit for converting said first power source voltage.

25. (New) The semiconductor integrated circuit device according to claim 21, wherein said electrostatic protection element clamps a voltage applied across said ground terminal and said power source wire at a clamp voltage, said clamp voltage being lower than a dielectric breakdown voltage of said MOS capacitor.

26. (New) The semiconductor integrated circuit device according to claim 21, wherein said electrostatic protection element is a MOS field effect transistor, the drain of which is connected to said power source wire, and the source and the gate of which are connected to said ground potential wire.

27. (New) The semiconductor integrated circuit device according to claim 21, wherein said electrostatic protection element is a bipolar transistor.

28. (New) The semiconductor integrated circuit device according to claim 21, wherein said electrostatic protection element is a thyristor.

29. (New) The semiconductor integrated circuit device according to claim 21, wherein said electrostatic protection element is a diode.